

Deep level system Gaussian approximation according the extrinsic photoconductivity in irradiated Si diodes.

Monday 23 May 2011 14:00 (20 minutes)

The WODEAN Si samples photoconductivity spectra were measured keeping the constant intensity of light at different wavelengths at low and medium temperatures. The deep level contribution was analysed by Lucovsky model proposing the Gaussian distribution of local level energies that followed from the preliminary results presented in the previous RD50 workshops. The time dependencies of photo-response at different excitation wavelength and TSC are presented and analyzed.

Author: Prof. VAITKUS, Juozas (Inst. of Appl. Res. (IAR) - Vilnius University)

Co-authors: Mr VAINORIUS, Neimantas (Vilnius University); Prof. KAZUKAUSKAS, Vaidotas (Vilnius University)

Presenter: Prof. VAITKUS, Juozas (Inst. of Appl. Res. (IAR) - Vilnius University)

Session Classification: Defect and Material Characterization